

Title of Invention: CLEANING SOLUTION FOR SEMICONDUCTOR
SUBSTRATE, METHOD FOR CLEANING TARGET OBJECT, AND METHOD FOR
MANUFACTURING SEMICONDUCTOR DEVICE

[Abstract]

The present invention provides a cleaning solution for a semiconductor substrate that, when used for a target object having a copper surface and a silicon carbonitride surface that have been subjected to chemical mechanical polishing processing, exhibits a high ability to clean the copper surface and the silicon carbonitride surface and is less corrosive to copper. The cleaning solution of the invention for a semiconductor substrate includes a compound represented by formula (A) and a polymer having a group selected from the group consisting of a carboxy group and salts thereof and a sulfonic acid group and salts thereof and has a pH of 7.5 or more.

No figure